



Capacitor-less LDO Regulator with High PSR Characteristics Ung Jae Ra, Jae Rim Baek, Hyunsun Mo, and Daejeong Kim* Dept. of Electrical Engineering, Kookmin University Seoul, Korea tyche@kookmin.ac.kr

Introduction

Power Management Integrated Circuit (PMIC)

• PMIC is an integrated circuit for power management and contains efficient control and management functions of the battery

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Proposed LDO regulator





Objective

- The switching frequency is increased to reduced the area of the DC-DC switching converter and increase efficiency
- In this paper, we proposed an capacitor-less LDO regulator with wideband PSR characteristic by canceling power supply noise without any hardware overhead or bandwidth limitations of additional analog circuits using High-pass filter and a single compensation transistor

Path that degrade PSR characteristic



Small signal equivalent circuit

•
$$\frac{v_{in} - v_{out}}{r_{op}} = \frac{v_{out}}{R_1 + R_2} + g_{mn} v_{out}$$

• $\frac{v_{out}}{v_{in}} = \frac{1}{1 + \frac{r_{op}}{R_1 + R_2} + g_{mn} r_{op}}$
• $PSR = 20 \log\left(\frac{v_{out}}{v_{in}}\right) = -20 \log\left(1 + \frac{r_{op}}{R_1 + R_2} + g_{mn} r_{op}\right)$

Simulation result & Experimental result





Four ripple paths that degrade the PSR characteristic

- Path I : Problem caused by ΔV_{gs} of power MOSFET because the loop bandwidth is not large enough as frequency increases
- Path II : Problem caused by ripple of input voltage transmitted to output node because small signal equivalent resistance(r_{op}) of power MOSFET is finite
- Path III : Problem caused by bandwidth limitation of error amplifier
- Path IV : Problem caused by bandwidth limitation of bandgap reference circuit(BGR)
- Path III and Path IV have no effect at high frequency region due to their own bandwidth limitation
- In order to obtain high PSR characteristic in a wide frequency region, it is necessary to solve the problems caused by Path I and Path II together

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Conclusion

The proposed LDO regulator is designed by adding a HPF and NMOS compensation transistor. A simple NMOS compensation transistor was added without any hardware overhead or additional amplifiers, confirming an PSR characteristic improvement of about 40 dB in the frequency region above 100MHz which is a problem for PSR characteristic

